











TPS82740A, TPS82740B

ZHCSCJ5A -JUNE 2014-REVISED JUNE 2014

TPS82740x 360nA I_Q MicroSIP™ 降压转换器模块

特性

- 360nA 静态电流典型值
- 10µA 输出电流时的效率高达 90%
- 引脚可选输出电压, 步长 100mV
- 集成转换率受控负载开关
- 高达 200mA 输出电流
- 2.2V 至 5.5V 的输入电压范围 V_{IN}
- 射频 (RF) 友好型 DCS-Control™
- 低输出电压纹波
- 自动转换至无纹波 100% 模式
- VOUT 和 LOAD 上的放电功能
- 高度不到 1.1mm 的解决方案
- 总体解决方案尺寸 < 6.7mm²
- 小型 2.3mm x 2.9mm MicroSIP™ 封装

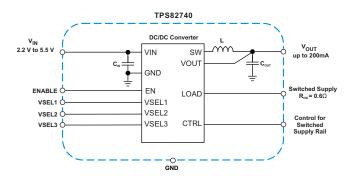
2 应用范围

- Bluetooth® 低功耗 (Low Energy), 消费类电子产品 用射频 (RF4CE), 短距低功耗通信协议 (Zigbee)
- 可穿戴电子产品
- 能量采集

3 说明

TPS82740 是业界第一款降压转换器模块,此模块特 有典型值为 360nA 的静态流耗。 它是一款用于超低功 率应用的完整 MicroSIPTM 直流/直流降压电源解决方 案。 此模块包括开关稳压器、电感器和输入/输出电容 器。将所有需要的无源组件集成在一起可实现仅为 6.7mm² 的微型解决方案尺寸。

典型应用



这款全新的基于 DCS-Control™ 的器件将轻负载效率 范围拓展至 10µA 负载电流以下。 它支持高达 200mA 的输出电流。

此器件由可再充电锂离子电池, 锂化学电池 (例如锂亚 硫酰氯 (Li-SOC12), 锂锰电池 (Li-MnO2)) 和两节或 三节碱性电池供电运行。 输入电压范围高达 5.5V, 也 可实现由 1 个 USB 端口和薄膜太阳能模块供电运行。

用户可通过三个电压选择引脚 (VSEL) 在 1.8V 至 2.5V (TPS82740A) 和 2.6V 至 3.3V (TPS82740B) 的范围 内以 100mV 的步长选择输出电压。 TPS82740 特有 低输出电压纹波和低噪声。 一旦电池电压接近输出电 压(接近 100% 占空比),此器件进入无纹波 100% 模式运行,以防止增加输出电压纹波。 在这个情况 下,此器件停止开关,并且输出被连接至输入电压。

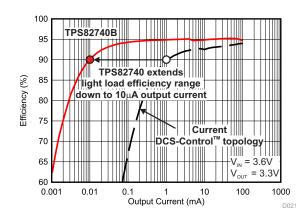
集成的转换率受控负载开关(具有 0.6Ω 的导通电阻典 型值)将已选输出电压配送至一个临时使用的子系统。

TPS82740 采用小型 9 焊锡凸点 6.7mm² MicroSiPTM 封装。

器件信息(1)

产品型号	封装	封装尺寸 (标称值)
TPS82740A	μSIP	2.30mm x 2.90mm
TPS82740B	μSIP	2.30mm x 2.90mm

(1) 要了解所有可用封装,请见数据表末尾的可订购产品附录。





目录 Functional Block Diagram 15 2 11 Application and Implementation...... 19 4 典型应用....... 1 5 修订历史记录 2 Device Comparison Table...... 3 12 Power Supply Recommendations 22 7 Pin Configuration and Functions 3 13 Layout...... 22 Specifications......4 13.1 Layout Guidelines 22 Absolute Maximum Ratings 4 8.1 13.2 Layout Example 22 8.2 Handling Ratings 4 Recommended Operating Conditions...... 4 8.3 14 器件和文档支持......24 8.5 商标.......24 Typical Characteristics......6 静电放电警告.......24 Parameter Measurement Information 14 术语表 24 10 Detailed Description 15 15 机械封装和可订购信息 24

5 修订历史记录

Changes from Original (June 2014) to Revision A			
•	Added 150 mA Typical current specification for I _{LIM softstart} , Low side MOSFET switch current limit	6	



6 Device Comparison Table

PART NUMBER	OUTPUT VOLTAGE SETTINGS (VSEL1, VSEL2, VSEL3)	PACKAGE MARKING
TPS82740A	1.8V to 2.5V in 100mV steps	E7
TPS82740B	2.6V to 3.3V in 100mV steps	E8

7 Pin Configuration and Functions

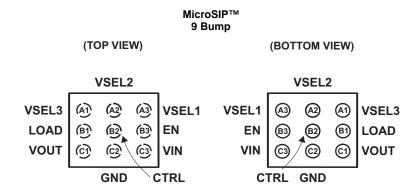


Table 1. Pin Functions

PI	N		
NAME	NO	1/0	DESCRIPTION
VIN	СЗ	IN	Input voltage supply pin of the module.
GND	C2	-	Ground terminal.
CTRL	B2	IN	CTRL pin controls the LOAD output pin. With CTRL = low, the LOAD output is disabled. This pin must be terminated and not left floating.
VOUT	C1	OUT	Output voltage pin of the module. An internal load switch is connected between VOUT pin and LOAD pin.
LOAD	B1	OUT	Load switch output pin controlled by the CTRL pin. With CTRL = high, an internal load switch connects the LOAD pin to the VOUT pin. The LOAD pin allows connect / disconnect other system components to the output of the DC/DC converter. This pin is pulled to GND with the CTRL pin = low. The LOAD pin features soft switching. If not used, leave the pin open.
VSEL3	A1	IN	Output voltage selection pins. See Table 2 and Table 3 for V _{OUT} selection. These pins must be terminated
VSEL2	A2	IN	and can be changed during operation.
VSEL1	A3	IN	
EN	В3	IN	High level enables the devices and low level turns the device into shutdown mode. This pin must be terminated and not left floating.

Table 2. Output Voltage Setting TPS82740A

Device	VOUT	VSEL3	VSEL2	VSEL1
1.8	1.8	0	0	0
	1.9	0	0	1
	2.0	0	1	0
TDC007404	2.1	0	1	1
TPS82740A	2.2	1	0	0
	2.3	1	0	1
	2.4	1	1	0
	2.5	1	1	1



Table 3. Output Voltage Setting TPS82740B

Device	VOUT	VSEL3	VSEL2	VSEL1
	2.6	0	0	0
	2.7	0	0	1
	2.8	0	1	0
TDC00740D	2.9	0	1	1
TPS82740B	3.0	1	0	0
	3.1	1	0	1
	3.2	1	1	0
	3.3	1	1	1

8 Specifications

8.1 Absolute Maximum Ratings⁽¹⁾

Over operating free-air temperature range (unless otherwise noted)

		VAI	.UE	UNIT
		MIN	MAX	
Pin voltage (2)	VIN	-0.3	6	V
	EN, CTRL, VSEL1, VSEL2, VSEL3	-0.3	V _{IN} +0.3V	V
	VOUT, LOAD	-0.3	3.7	V
Operating ambient	temperature range, T _A ⁽³⁾	-40	85	°C
Operating junction	temperature T _J	-40	125	°C

⁽¹⁾ Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute—maximum—rated conditions for extended periods may affect device reliability.

(2) All voltage values are with respect to network ground terminal GND.

8.2 Handling Ratings

			MIN	MAX	UNIT
T _{stg}	Storage temperature range		- 55	125	°C
V	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins (1)	0	2000	V
V _(ESD)		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins (2)	0	1000	V

JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. The human body model is a 100-pF capacitor discharged through a 1.5-kΩ resistor into each pin.

8.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
V _{IN}	Supply voltage V _{IN}		2.2		5.5	٧
I _{OUT} + I _{LOAD}	Device output current (sum of I _{OUT} and I _{LOAD})	$V_{OUTnom} + 0.7V \le V_{IN} \le 5.5V$			200	mA
		$V_{OUTnom} \le V_{IN} \le V_{OUTnom} + 0.7V$			100	
I _{LOAD}	Load current (current from LOAD pin)	,			100	
C _{OUT}	Additional output capacitance connected to VOUT	pin (not including LOAD pin)			10	μF
C _{LOAD}	Capacitance connected to LOAD pin				10	
T _J	Operating junction temperature range		-40		90	°C
T _A	Operating ambient temperature range		-40		85	

⁽³⁾ In applications where ambient temperature (T_A) constantly stays above 70°C, the product life time might degrade. MLCC capacitor reliability and lifetime is depending on temperature and applied voltage conditions. At higher temperatures, MLCC capacitors are subject to stronger stress. The most critical parameter is the Insulation Resistance (IR) resulting in leakage current.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



8.4 Thermal Information

		TPS82740	
	THERMAL METRIC ⁽¹⁾	μSIP	UNIT
		9 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	83	
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	53	
$R_{\theta JB}$	Junction-to-board thermal resistance	-	°C/W
ΨЈТ	Junction-to-top characterization parameter	-	C/VV
ΨЈВ	Junction-to-board characterization parameter	-	
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	-	

⁽¹⁾ For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

8.5 Electrical Characteristics

 $V_{IN} = 3.6V$, $T_{A} = -40$ °C to 85°C, typical values are at $T_{A} = 25$ °C (unless otherwise noted)

PA	RAMETER	TEST CONDITIONS		MIN TYP	MAX	UNIT
SUPPLY			'			
V _{IN}	Input voltage range			2.2	5.5	V
		$EN = V_{IN}$, $CTRL = GND$, $I_{OUT} = 0\mu A$, $V_{OUT} =$ switching	1.8V / 2.6V, device not	360	2300	
		EN = V _{IN} , I _{OUT} = 0mA, CTRL = GND, V _{OUT} =	1.8V device switching	460		nA
lα	Operating quiescent	EN = V _{IN} , I _{OUT} = 0mA, CTRL = GND, V _{OUT} =	2.6V, device switching	500		
·u	current	$EN = V_{IN}$, $I_{OUT} = 0$ mA., $CTRL = V_{IN}$, $V_{OUT} = 1$ switching	.8V, device not	12.5		μA
		$EN = V_{IN}$, $I_{OUT} = 0$ mA., $CTRL = V_{IN}$, $V_{OUT} = 2$ switching	.6V, device not	13.5		μА
I _{SD}	Shutdown current	EN = GND, shutdown current into V _{IN}		70		nΛ
		EN = GND, shutdown current into V _{IN} , T _A = 60°C		150		nA
V _{TH_UVLO+}	Undervoltage	Rising V _{IN}		2.075	2.15	V
V _{TH_UVLO} -	lockout threshold	Falling V _{IN}		1.925	2	V
INPUTS EN, CTRL,	VSEL 1-3					
V _{IH TH}	High level input threshold	$2.2 \text{V} \leq \text{V}_{\text{IN}} \leq 5.5 \text{V}$			1.1	V
V _{IL TH}	Low level input threshold	$2.2 \text{V} \leq \text{V}_{\text{IN}} \leq 5.5 \text{V}$		0.4		V
I _{IN}	Input bias Current	T _A = 25°C			10	nA
		$T_A = -40$ °C to 85°C			25	
POWER SWITCHES	S		·			
	High side MOSFET switch current limit	0.00/2// 25.57/		430		mA
I _{LIMF}	Low side MOSFET switch current limit	$2.2V \le V_{\text{IN}} \le 5.5V$		430		mA
OUTPUT DISCHAR	GE SWITCH (VOUT)				·	
R _{DSCH_VOUT}	MOSFET on- resistance	EN = GND, I _{OUT} = -10mA into VOUT pin		30	65	Ω
	Bias current into	EN V V 2V/2 9V CTDL CND	T _A = 25°C	40	660	A
I _{IN_VOUT}	VOUT pin	$EN = V_{IN}$, $V_{OUT} = 2V / 2.8V$, $CTRL = GND$	$T_A = -40$ °C to 85°C		1570	nA
LOAD OUTPUT (LO	DAD)					
R _{LOAD}	High side MOSFET on-resistance	$I_{LOAD} = 50$ mA, CTRL = V_{IN} , $V_{OUT} = 2.0$ V / 2.8 V, 2.2 V $\leq V_{IN} \leq 5.5$ V		0.6	1.25	Ω
R _{DSCH_LOAD}	Low side MOSFET on-resistance	CTRL = GND, 2.2V ≤ V _{IN} ≤ 5.5V, I _{LOAD} = - 10mA		30	65	
t _{Rise_LOAD}	V _{LOAD} rise time	Starting with CTRL low to high transition, tim 0V to 95%, $V_{OUT} = 1.8V / 2.6V$, $2.2V \le V_{IN} \le 25^{\circ}C$		315	800	μs



Electrical Characteristics (continued)

 $V_{IN} = 3.6V$, $T_A = -40$ °C to 85°C, typical values are at $T_A = 25$ °C (unless otherwise noted)

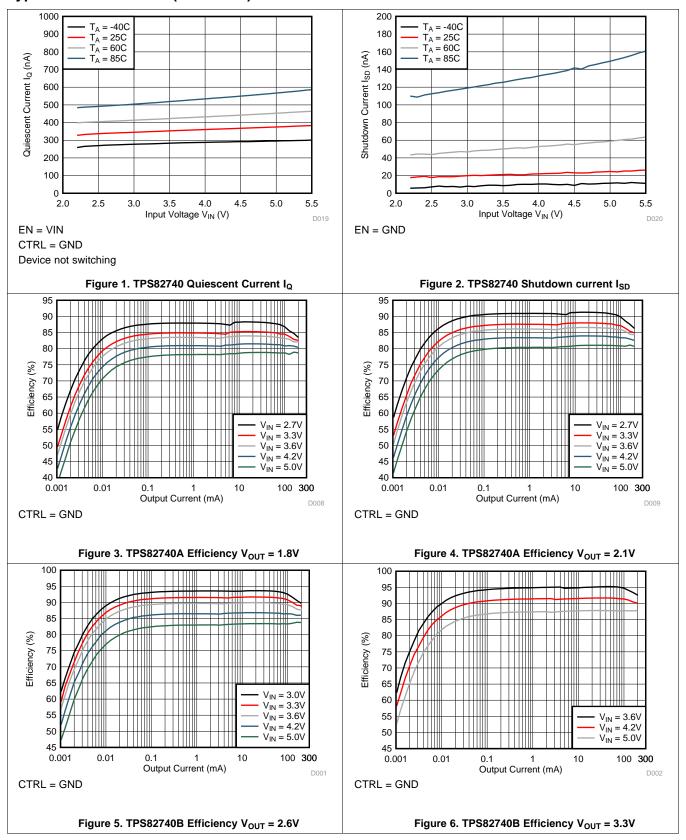
PAR	RAMETER	TEST CONDITIONS		MIN TYP MAX		UNIT	
AUTO 100% MODE	TRANSITION					•	
V _{TH_100+}	Auto 100% Mode exit detection threshold ⁽¹⁾	Rising V_{IN} ,100% Mode is left with $V_{IN} = V_{OUT} + V_{OUT}$ at $T_J = 85^{\circ}C$	TH_100+ , max value	170	250	340	mV
V _{TH_100} -	Auto 100% Mode enter detection threshold ⁽¹⁾	Falling V_{IN} , 100% Mode is entered with $V_{IN} = V_{OL}$ value at $T_J = 85$ °C	_{JT} + V _{TH_100-} , max	110	200	280	
OUTPUT						•	
t _{Startup_delay}	Regulator start up delay time	From transition EN = low to high until device star	ts switching		10	25	ms
t _{Softstart}	Softstart time with reduced switch current limit	$2.2V \le V_{IN} \le 5.5V$, EN = V_{IN}			400	1200	μs
1	High side MOSFET switch current limit	Reduced switch current limit during softstart		80	150	200	mA
ILIM_softstart	Low side MOSFET switch current limit	Reduced switch current limit during solistant			150		mA
	Output voltage	Output voltages are selected with pins VSEL1,	TPS82740A	1.8		2.5	V
	range	VSEL2, VSEL3	TPS82740B	2.6		3.3	
	Output voltage	I _{OUT} = 10mA, V _{OUT} = 1.8V / 2.6V		-2.5	0	2.5	%
V _{VOUT}	accuracy	I _{OUT} = 100mA, V _{OUT} = 1.8V / 2.6V		-2	0	2	
	DC output voltage load regulation	V _{OUT} = 1.8V / 2.6V, CTRL = V _{IN}			0.001		%/mA
	DC output voltage line regulation	$V_{OUT} = 1.8V / 2.6V$, CTRL = V_{IN} , $I_{OUT} = 10$ mA, 2	.5V ≤ V _{IN} ≤ 5.5V		0		%/V

⁽¹⁾ V_{IN} is compared to the programmed output voltage (V_{OUT}). When V_{IN} – V_{OUT} falls below V_{TH_100-} , the device enters 100% Mode by turning the high side MOSFET on. 100% Mode is exited when V_{IN} – V_{OUT} exceeds V_{TH_100+} and the device starts switching. The hysteresis for the 100% Mode detection threshold V_{TH_100+} - V_{TH_100-} is always positive and 50 mV(typ.)

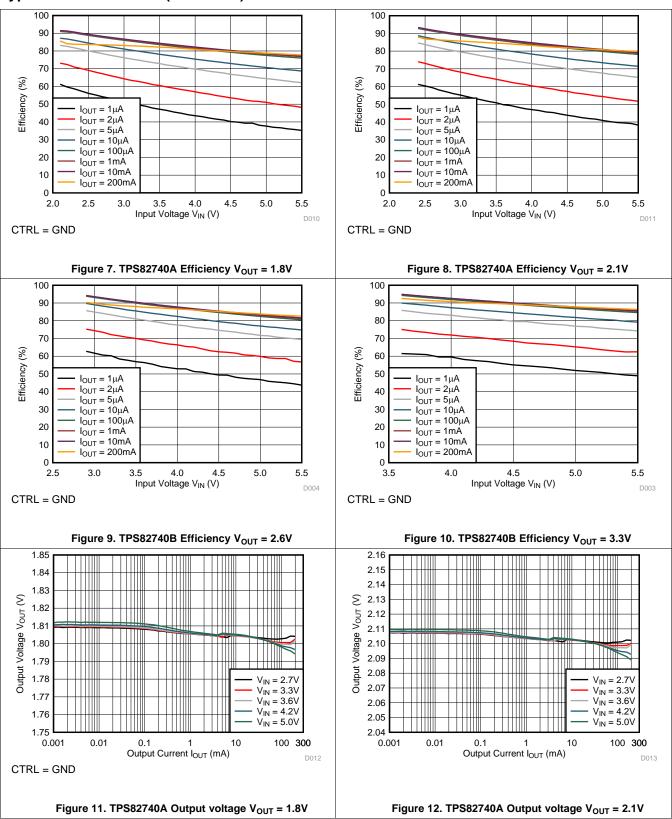
8.6 Typical Characteristics

TABLE OF	GRAPHS		FIGURE
η	Efficiency	vs Output Current	Figure 3, Figure 4, Figure 5, Figure 6
η	Efficiency	vs Input Voltage	Figure 7, Figure 8, Figure 9, Figure 10
V _{OUT}	Output voltage	vs Output curent	Figure 11, Figure 12, Figure 13, Figure 14
IQ	Operating quiescent current	vs Input voltage	Figure 1
I _{SD}	Shutdown current	vs Input voltage	Figure 2
	Automatic Transition into 100% Mode		Figure 18, Figure 19, Figure 20
F _{SW}	Switching frequency	vs Output current	Figure 15, Figure 16, Figure 17
	Line and Load Transient Performance		Figure 21, Figure 22, Figure 23, Figure 24, Figure 25, Figure 26, Figure 27, Figure 28, Figure 29, Figure 30
	AC load regulation performance		Figure 31, Figure 32
LOAD	LOAD Output Behavior		Figure 33, Figure 34, Figure 35
	Input Voltage Ramp up / down		Figure 36, Figure 37, Figure 38, Figure 39

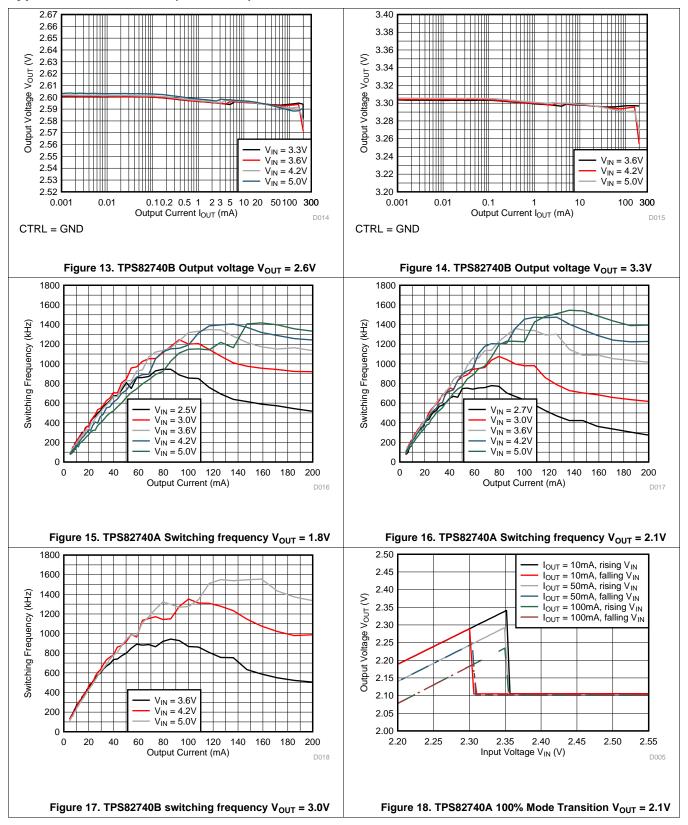




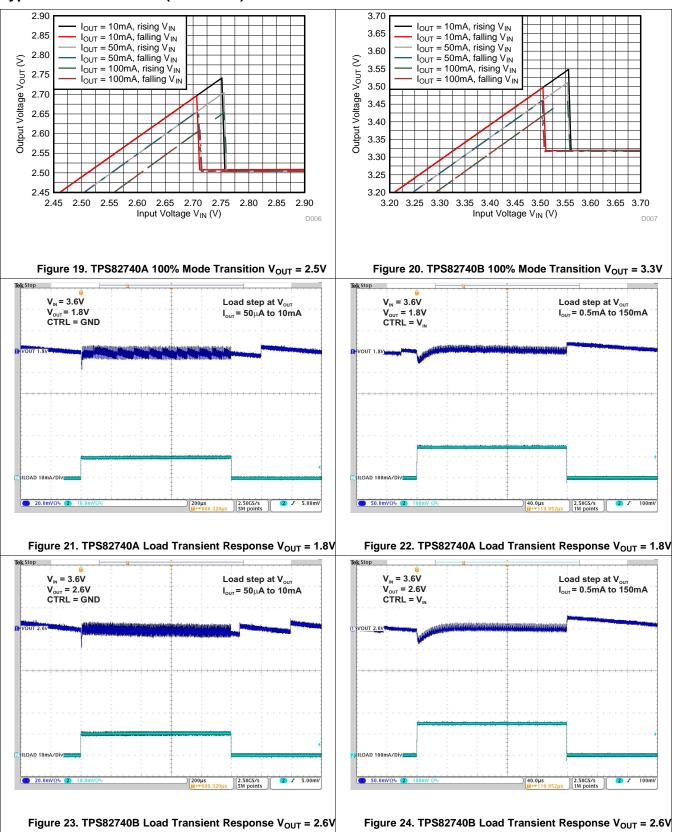
TEXAS INSTRUMENTS



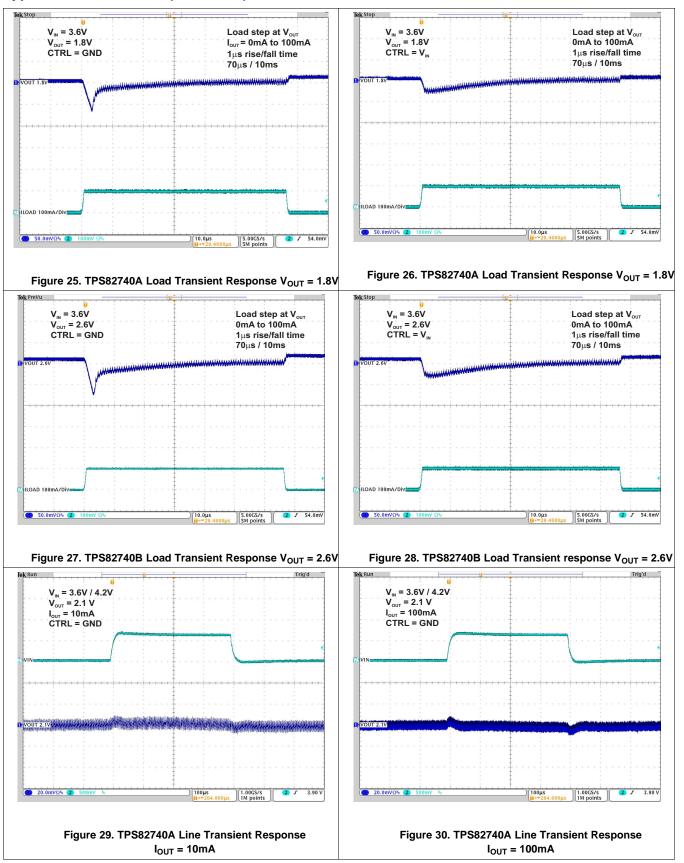




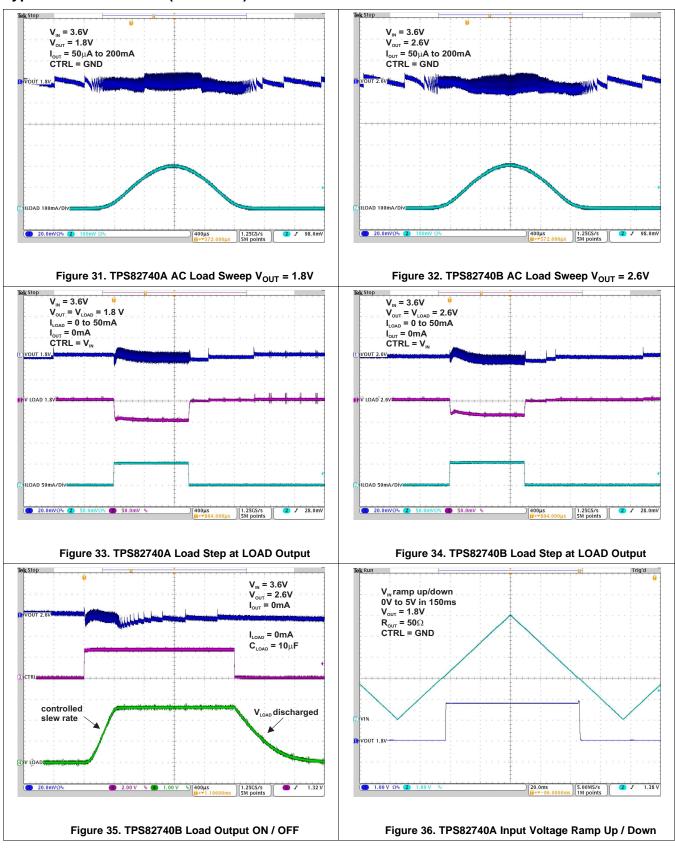
TEXAS INSTRUMENTS



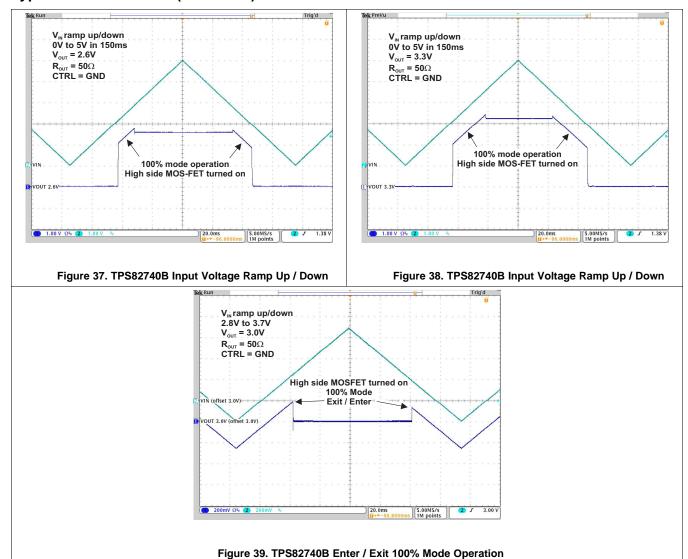




TEXAS INSTRUMENTS

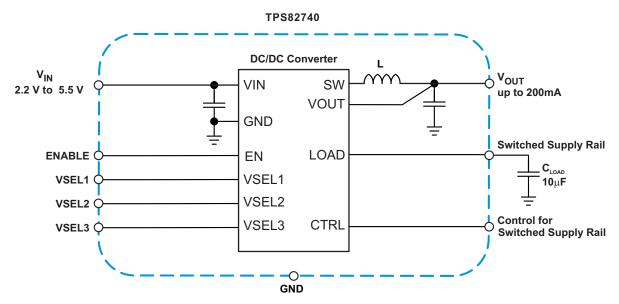








9 Parameter Measurement Information



Measurement Configuration with Passive Components

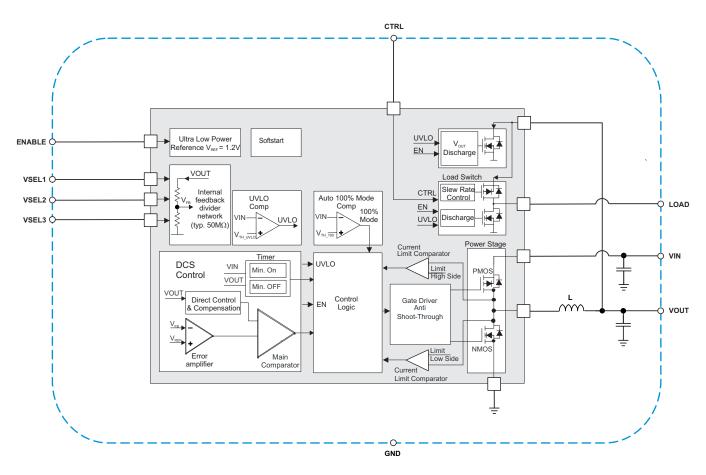


10 Detailed Description

10.1 Overview

The TPS82740 is the first fully integrated step down converter module with an ultra low quiescent current consumption (360nA typ.) while maintaining a regulated output voltage and featuring TI's DCS-Control™ topology. The device extends high efficiency operation to output currents down to a few micro amperes.

10.2 Functional Block Diagram



10.3 Feature Description

10.3.1 DCS-Control™

TI's DCS-Control™ (Direct Control with Seamless Transition into Power Save Mode) is an advanced regulation topology, which combines the advantages of hysteretic and voltage mode control. Characteristics of DCS-Control™ are excellent AC load regulation and transient response, low output ripple voltage and a seamless transition between PFM and PWM mode operation. DCS-Control™ includes an AC loop which senses the output voltage (VOUT pin) and directly feeds the information to a fast comparator stage. This comparator sets the switching frequency, which is constant for steady state operating conditions, and provides immediate response to dynamic load changes. In order to achieve accurate DC load regulation, a voltage feedback loop is used.

The DCS-Control™ topology supports PWM (Pulse Width Modulation) mode for medium and high load conditions and Power Save Mode at light loads. During PWM mode, it operates in continuous conduction. The switching frequency goes up to 1.7MHz with a controlled frequency variation depending on the input voltage. If the load current decreases, the converter seamlessly enters Power Save Mode to maintain high efficiency down to very light loads. In Power Save Mode, the switching frequency varies nearly linearly with the load current. Since DCS-Control™ supports both operation modes within one single building block, the transition from PWM to Power Save Mode is seamless without effects on the output voltage. The TPS82740 offers both excellent DC



Feature Description (continued)

voltage and superior load transient regulation, combined with very low output voltage ripple, minimizing interference with RF circuits. At high load currents, the converter operates in quasi fixed frequency PWM mode operation and at light loads in PFM (Pulse Frequency Modulation) mode to maintain highest efficiency over the full load current range. In PFM Mode, the device generates a single switching pulse to ramp up the inductor current and recharge the output capacitor, followed by a sleep period where most of the internal circuits are shutdown to achieve the lowest quiescent current. During this time, the load current is supported by the output capacitor. The duration of the sleep period depends on the load current and the inductor peak current.

During the sleep periods, the quiescent current of the TPS82740 is reduced to 360nA. This low quiescent current consumption is achieved by an ultra low power voltage reference, an integrated high impedance (typ. $50M\Omega$) feedback divider network and an optimized DCS-ControlTM block.

10.3.2 LOAD Switch

The LOAD pin can be used to power an additional, temporarily used sub-system. If the CTRL pin is set high, the LOAD pin is connected to the VOUT pin via an integrated load switch. The load switch is slew rate controlled to support soft switching and not impacting the regulated output VOUT. If the CTRL pin is set to low, the LOAD pin is disconnected from the VOUT pin and internally connected to GND by an internal discharge switch. The CTRL pin can be controlled by a micro controller and must be terminated. With CTRL pin high, the quiescent current is increased to improve the transient response.

10.3.3 Output Voltage Selection (VSEL1, VSEL2, VSEL3)

The TPS82740 provides an integrated, high impedance (typ. $50M\Omega$) feedback resistor divider network which is programmed by the pins VSEL1-3. The TPS82740A supports an output voltage range of 1.8V to 2.5V in 100mV steps, while the TPS82740B supports an output voltage range from 2.6V to 3.3V in 100mV steps. The output voltage can be changed during operation and supports a simple dynamic output voltage scaling, shown in Figure 44. The output voltage is programmed according to Table 2 and Table 3.

10.3.4 Output Discharge Function (VOUT and LOAD)

Both the VOUT pin and the LOAD pin feature a discharge circuit to connect each rail to GND, once they are disabled. This feature prevents residual charge voltages on capacitors connected to these pins, which may impact proper power up of the main- and sub-system. With the CTRL pin pulled low, the discharge circuit at the LOAD pin activates. With the EN pin pulled low, the discharge circuit at the pin VOUT activates.

10.3.5 Internal Current Limit

The TPS82740 integrates a current limit in the high side, as well as in the low side MOSFETs to protect the device against overload or short circuit conditions. The peak current in the switches is monitored cycle by cycle. If the high side MOSFET current limit is reached, the high side MOSFET is turned off and the low side MOSFET is turned on until the current decreases below the low side MOSFET current limit.

Table 4. Load Pin Condition Table

	Pin con	dition	Operating condition	Remark
LOAD	EN	CTRL	VIN	
Connected to VOUT	high	high	> V _{UVLO}	load switch enabled and slew rate controlled
	high	low	> V _{UVLO}	load switch turned off
Connected to GND	low	high or low	> V _{UVLO}	device and load switch disabled
	high	high	< V _{UVLO}	device disabled due to UVLO



10.3.6 CTRL / DVS (Dynamic Voltage Scaling TPS62741)

In TPS62741, the CTRL pin controls beside the load switch as well Dynamic Voltage Scaling. The CTRL pin selects between two different voltage setting banks. The voltage of each bank are set with the VSEL pins 1-4 according to .

The output LOAD is controlled with the CTRL pin. The pin is internally connected either to VOUT pin or GND and can be used to power up/down temporarily used external circuits to reduce leakage current consumption of the system.

10.4 Device Functional Modes

10.4.1 Enable / Shutdown

The TPS82740 is activated when the EN pin is set high. For proper operation, the pin must be terminated and must not be left floating. With the EN pin set low, the device enters shutdown mode with less than typ. 70nA current consumption.

10.4.2 Softstart

When the device is enabled, the internal reference is powered up and after the startup delay time $t_{Startup_delay}$ has expired, the device enters softstart, starts switching and ramps up the output voltage. During softstart, the device operates with a reduced current limit, $I_{LIM_softstart}$, of typ. 1/3 of the nominal current limit. This reduced current limit is active during the time $t_{Softstart}$. The current limit is increased to its nominal value, I_{LIMF} , once this time has expired or the nominal output voltage is reached.

10.4.3 POWER GOOD OUTPUT (PG)

The Power Good comparator features an open drain output. The PG comparator is active with EN pin set to high and V_{IN} is above the threshold V_{TH_UVLO+} . It is driven to high impedance once V_{OUT} trips the threshold V_{TH_PG+} for rising V_{OUT} . The output is pulled to low level once V_{OUT} falls below the PG hysteresis, V_{PG_hys} . The output is also pulled to low level in case the input voltage V_{IN} falls below the undervoltage lockout threshold V_{TH_UVLO-} or the device is disabled with EN = low. The power good output (PG) can be used as an indicator for the system to signal that the converter has started up and the output voltage is in regulation.

Operating condition Pin condition Remark PG ΕN **CTRL** IOUT / ILOAD VIN **VOUT** PG comparator hiz high high don't care $> V_{UVLO}$ VOUT > V_{TH PG+} active, pull up resistor pulls PG to high PG comparator medium load (> active, pull up resistor hiz high VOUT > V_{TH PG+} low > V_{UVLO} 1mA) pulls PG to high PG comparator disabled for low Iq hiz high low light load (< 1mA) $> V_{UVLO}$ VOUT > V_{TH PG+} operation, pull up resistor pulls PG to high 0mA < IOUT < startup, overload or $VOUT < V_{TH_PG}$ high don't care low > V_{UVLO} 100mA ramp down output disabled $V_{IN} > 1.2V$ VOUT = 0device disabled low low don't care device disabled, due low high don't care output disabled $< V_{UVLO}$ VOUT not present to UVLO

Table 5. PG condition table

Table 6. VOUT Output Discharge Condition Table

VOUT pin	EN	VIN condition	remark
connected to GND, output discharged	low	1.5V < V _{IN} < V _{UVLO}	
connected to GND, output discharged	high	< V _{UVLO}	



Table 6. VOUT Output Discharge Condition Table (continued)

VOUT pin	EN	VIN condition	remark
hiz, discharge switch disabled	high	> V _{UVLO}	during regulator start up, the discharge switch is enabled and VOUT pulled to low, until the regulator start up time t _{Start} expires. During the softstart time and later, the discharge switch is disabled.

10.4.4 Automatic Transition into 100% Mode

Once the input voltage comes close to the output voltage, the TPS82740 stops switching and enters 100% duty cycle operation. It connects the output VOUT via the inductor and the internal high side MOSFET switch to the input VIN, once the input voltage V_{IN} falls below the 100% mode enter threshold, V_{TH_100} . In 100% mode switching stops eliminating output voltage ripple. Because the output is connected to the input, the output voltage tracks the input voltage minus the voltage drop across the internal high side switch and the inductor caused by the output current. Once the input voltage increases and trips the 100% mode exit threshold, V_{TH_100+} , the TPS82740 turns on and starts switching again. See Figure 40, Figure 18, Figure 19 and Figure 20.

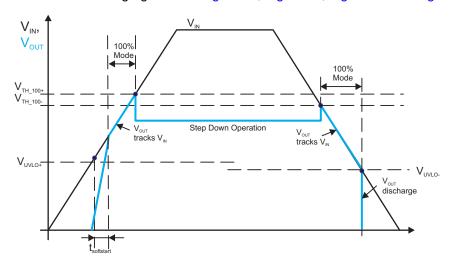


Figure 40. Automatic Transition into 100% Mode



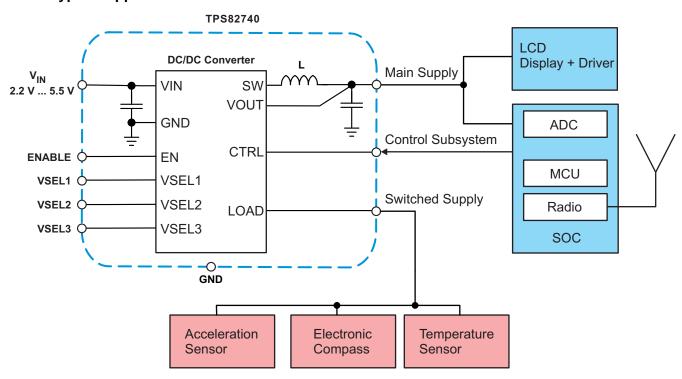
11 Application and Implementation

11.1 Application Information

The device is designed to operate from an input voltage supply range between 2.2V and 5.5V with a maximum output current of 200mA. Once the input voltage comes close to the output voltage, the DC/DC converter stops switching and enters 100% duty cycle operation. The integrated slew rate controlled load switch can distribute the selected output voltage to a temporarily used sub-system. The TPS82740 module operates in PWM mode for medium and high load conditions and in power save mode at light load currents.

At high load currents, the converter operates in quasi fixed frequency PWM mode operation. The switching frequency is up to 1.7MHz with a controlled frequency variation depending on the input voltage. If the load current decreases, the converter seamlessly enters Power Save Mode by varying the switching frequency linearly to maintain high efficiency over the full load current range. At very light load conditions the device generates a single switching pulse to ramp up the inductor current and recharge the output capacitor, followed by a sleep period where most of the internal circuits are shutdown to achieve 360nA quiescent current consumption.

11.2 Typical Application



Example of Implementation in a SOC Based System

11.2.1 Design Requirements

TPS82740 is a complete step-down converter module including all passive components (inductor, input and output capacitor). For most applications no additional input / output capacitors are required. Use the following typical application design procedure to select additional external components in case further performance improvement of the module is desired.

11.2.2 Detailed Design Procedure

11.2.2.1 Input Capacitor Selection

For most applications, the integrated input capacitor at the VIN pin is sufficient.

Typical Application (continued)

TPS82740 uses a tiny ceramic input capacitor. When a ceramic capacitor is combined with trace or cable inductance, such as that from a wall adapter, a load step at the output can induce ringing at the VIN pin. This ringing can couple to the output and be mistaken as loop instability or can even damage the module. In this circumstance, additional ceramic 'bulk" capacitance, such as electrolytic or tantalum, should be placed between the input of the module and the power source lead to reduce ringing that occurs between the inductance of the power source leads and the module.

11.2.2.1.1 Input Buffer Capacitor Selection

In addition to the small ceramic input capacitor a larger buffer capacitor C_{Buf} is recommended to reduce voltage drops and ripple voltage. When using battery chemistries like Li-SOCI2, Li-SO2, Li-MnO2, the impedance of the battery has to be considered. These battery types tend to increase their impedance depending on discharge status and often can support output currents of only a few mA. Therefore a buffer capacitor is recommended to stabilize the battery voltage during DC/DC operations e.g. for a RF transmission. A voltage drop on the input of the TPS82740 during DC/DC operation impacts the advantage of the step down conversion for system power reduction. Furthermore the voltage drops can fall below the minimum recommended operating voltage of the device and leads to an early system cut off. Both effects reduce the battery life time. To achieve best performance and to extract the most energy out of the battery a good procedure is to select the buffer capacitor value for an voltage drop below 50mVpp during DC/DC operation. The capacitor value strongly depends on the used battery type, as well the current consumption during a RF transmission as well the duration of the transmission.

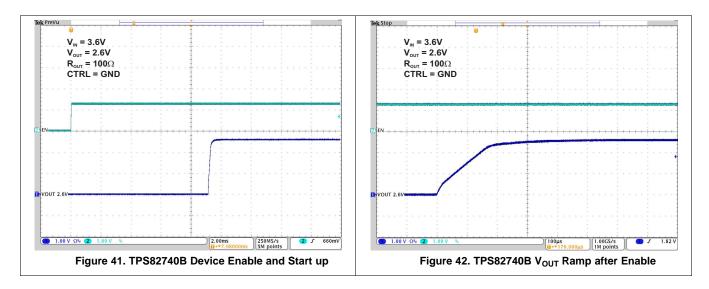
11.2.2.2 Output Capacitor Selection

For most applications, the integrated output capacitor at the VOUT pin is sufficient.

In order to further reduce the output voltage ripple and improve the load transient performance an additional external output capacitance may be used. For most applications an additional $4.7\mu F$ or $10\mu F$ capacitor will be sufficient. Care should be taken that the total effective capacitance present at the output does not exceed $10\mu F$ in order to guarantee loop stability. Ceramic capacitors with low ESR values have the lowest output voltage ripple and are recommended.

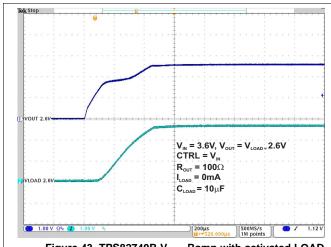
At the LOAD output pin, no additional output capacitor is required. For applications demanding external capacitance connected to the LOAD pin, the total capacitance should not exceed $10\mu F$.

11.2.3 Application Curves





Typical Application (continued)





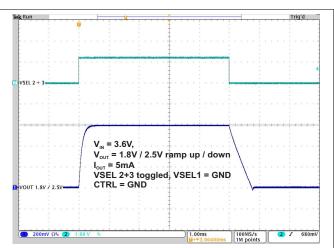


Figure 44. TPS82740A Dynamic Output Voltage Scaling: $V_{OUT} = 1.8V / 2.5V$



12 Power Supply Recommendations

The TPS82740 device is a complete and optimized power supply module working within the given specification range without additional components. Please use the information given in the Application Information section to connect the input and output circuitry appropriately.

13 Layout

13.1 Layout Guidelines

In making the pad size for the uSiP LGA balls, it is recommended that the layout use a non-solder-mask defined (NSMD) land. With this method, the solder mask opening is made larger than the desired land area, and the opening size is defined by the copper pad width. Figure 45 shows the appropriate diameters for a MicroSiPTM layout. Figure 46 shows a suggestion for the PCB layout.

13.2 Layout Example

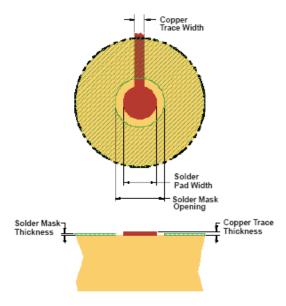


Figure 45. Recommended Land Pattern Image and Dimensions

SOLDER PAD DEFINITIONS ⁽¹⁾⁽²⁾⁽³⁾⁽⁴⁾			COPPER THICKNESS	STENCIL ⁽⁶⁾ OPENING	STENCIL THICKNESS	
Non-solder-mask defined (NSMD)	0.30mm	0.360mm	1oz max (0.032mm)	0.34mm diameter	0.1mm thick	

- (1) Circuit traces from non-solder-mask defined PWB lands should be 75µm to 100µm wide in the exposed area inside the solder mask opening. Wider trace widths reduce device stand off and affect reliability.
- (2) Best reliability results are achieved when the PWB laminate glass transition temperature is above the operating the range of the intended application.
- (3) Recommend solder paste is Type 3 or Type 4.
- (4) For a PWB using a Ni/Au surface finish, the gold thickness should be less than 0.5mm to avoid a reduction in thermal fatigue performance.
- (5) Solder mask thickness should be less than 20 μm on top of the copper circuit pattern.
- (6) For best solder stencil performance use laser cut stencils with electro polishing. Chemically etched stencils give inferior solder paste volume control.



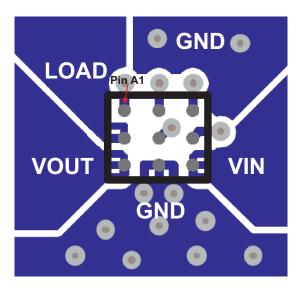


Figure 46. PCB Layout Suggestion

13.3 Surface Mount Information

The TPS82740 MicroSIP™ module uses an open frame construction for a fully automated assembly process and provides a large surface area for pick and place operations. See the "Pick Area" in the package drawing.

Package height and weight have been kept to a minimum, allowing MicroSIP™ device handling similar to a 0805 footprint component.

For reflow recommendations, see document J-STD-20 from the JEDEC/IPC standard.



14 器件和文档支持

14.1 文档支持

14.1.1 相关链接

以下表格列出了快速访问链接。 范围包括技术文档、支持与社区资源、工具和软件,以及样片或购买的快速访问。

表 7. 相关链接

部件	产品文件夹	样片与购买	技术文档	工具与软件	支持与社区
TPS82740A	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处
TPS82740B	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处

14.2 商标

DCS-Control, MicroSIP are trademarks of Texas Instruments. is a registered trademark of ~Bluetooth SIG, Inc..

14.3 静电放电警告



这些装置包含有限的内置 ESD 保护。 存储或装卸时,应将导线一起截短或将装置放置于导电泡棉中,以防止 MOS 门极遭受静电损伤。

14.4 术语表

SLYZ022 — TI 术语表。

这份术语表列出并解释术语、首字母缩略词和定义。

15 机械封装和可订购信息

以下页中包括机械封装和可订购信息。 这些信息是针对指定器件可提供的最新数据。 这些数据会在无通知且不对本文档进行修订的情况下发生改变。 欲获得该数据表的浏览器版本,请查阅左侧的导航栏。

www.ti.com

3-Aug-2025

PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking
	(1)	(2)			(3)	(4)	(5)		(6)
TPS82740ASIPR	Active	Production	uSiP (SIP) 9	3000 LARGE T&R	Yes	NIAU	Level-2-260C-1 YEAR	-40 to 85	E7 TXI740XEC
TPS82740ASIPR.B	Active	Production	uSiP (SIP) 9	3000 LARGE T&R	-	Call TI	Call TI	-40 to 125	
TPS82740ASIPT	Active	Production	uSiP (SIP) 9	250 SMALL T&R	Yes	NIAU	Level-2-260C-1 YEAR	-40 to 85	E7 TXI740XEC
TPS82740ASIPT.B	Active	Production	uSiP (SIP) 9	250 SMALL T&R	-	Call TI	Call TI	-40 to 125	
TPS82740BSIPR	Active	Production	uSiP (SIP) 9	3000 LARGE T&R	Yes	NIAU	Level-2-260C-1 YEAR	-40 to 85	E8 TXI2743EC
TPS82740BSIPR.B	Active	Production	uSiP (SIP) 9	3000 LARGE T&R	-	Call TI	Call TI	-40 to 125	
TPS82740BSIPT	Active	Production	uSiP (SIP) 9	250 SMALL T&R	Yes	NIAU	Level-2-260C-1 YEAR	-40 to 85	E8 TXI2743EC
TPS82740BSIPT.B	Active	Production	uSiP (SIP) 9	250 SMALL T&R	-	Call TI	Call TI	-40 to 125	

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.



PACKAGE OPTION ADDENDUM

www.ti.com 3-Aug-2025

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

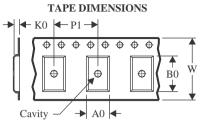
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com 17-Mar-2023

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

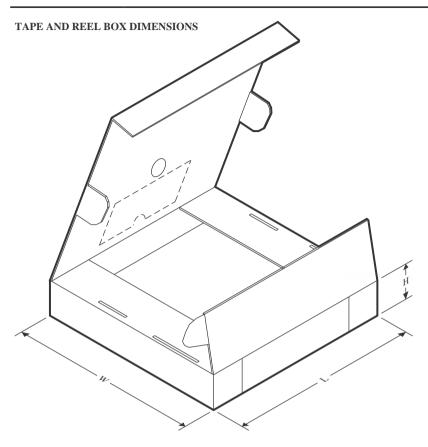


*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS82740ASIPR	uSiP	SIP	9	3000	178.0	9.0	2.5	3.1	1.35	4.0	8.0	Q2
TPS82740ASIPT	uSiP	SIP	9	250	178.0	9.0	2.83	3.18	1.2	4.0	8.0	Q2
TPS82740BSIPR	uSiP	SIP	9	3000	178.0	9.0	2.5	3.1	1.35	4.0	8.0	Q2
TPS82740BSIPT	uSiP	SIP	9	250	178.0	9.0	2.83	3.18	1.2	4.0	8.0	Q2



www.ti.com 17-Mar-2023



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS82740ASIPR	uSiP	SIP	9	3000	223.0	194.0	35.0
TPS82740ASIPT	uSiP	SIP	9	250	223.0	194.0	35.0
TPS82740BSIPR	uSiP	SIP	9	3000	223.0	194.0	35.0
TPS82740BSIPT	uSiP	SIP	9	250	223.0	194.0	35.0

重要通知和免责声明

TI"按原样"提供技术和可靠性数据(包括数据表)、设计资源(包括参考设计)、应用或其他设计建议、网络工具、安全信息和其他资源,不保证没有瑕疵且不做出任何明示或暗示的担保,包括但不限于对适销性、某特定用途方面的适用性或不侵犯任何第三方知识产权的暗示担保。

这些资源可供使用 TI 产品进行设计的熟练开发人员使用。您将自行承担以下全部责任:(1) 针对您的应用选择合适的 TI 产品,(2) 设计、验证并测试您的应用,(3) 确保您的应用满足相应标准以及任何其他功能安全、信息安全、监管或其他要求。

这些资源如有变更,恕不另行通知。TI 授权您仅可将这些资源用于研发本资源所述的 TI 产品的相关应用。 严禁以其他方式对这些资源进行复制或展示。您无权使用任何其他 TI 知识产权或任何第三方知识产权。您应全额赔偿因在这些资源的使用中对 TI 及其代表造成的任何索赔、损害、成本、损失和债务,TI 对此概不负责。

TI 提供的产品受 TI 的销售条款或 ti.com 上其他适用条款/TI 产品随附的其他适用条款的约束。TI 提供这些资源并不会扩展或以其他方式更改 TI 针对 TI 产品发布的适用的担保或担保免责声明。

TI 反对并拒绝您可能提出的任何其他或不同的条款。

邮寄地址:Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 版权所有 © 2025,德州仪器 (TI) 公司